

REMARKS

Applicants respectfully request favorable reconsideration of this application, as amended.

Claims 1-18 are pending. By this Amendment, Claims 1 and 6 have been amended to correct minor editorial errors.

In the Office Action, Claim 1 was apparently rejected under 35 U.S.C. § 103 over Takashi in combination with Kinoshita, and Claims 2-18 were rejected under 35 U.S.C. § 103 over Takashi and Kinoshita in further combination with Moyer. Applicants respectfully traverse these rejections.

Independent Claim 1 recites, *inter alia*, a plurality of bipolar transistors that are provided on a semiconductor layer such that collectors, emitters and bases of the bipolar transistors are respectively connected in parallel with each other. An isolation is provided over a main surface of the semiconductor layer to reach the insulation layer, and provided such that the isolation surrounds a group of or the whole of the plurality of bipolar transistors, such that the surrounded transistors operate substantially uniformly as constituent elements of a unit transistor.

As acknowledged in the Office Action, Takashi fails to teach, or suggest a semiconductor device in which the collectors, emitters, and bases of the bipolar transistors

are respectively connected in parallel with each other, as recited in independent Claim 1. However, the Office Action alleges that Kinoshita teaches this feature and that it would have been obvious to one skilled in the art to combine Takashi and Kinoshita to achieve the invention of Claims 1, 6 and 10. Applicants respectfully disagree.

Takashi evidently teaches a fundamentally different arrangement from Applicants' invention as defined in Claim 1. Referring to Takashi's Fig. 6 cited in the outstanding rejection, note that the portion of Takashi relied upon in the Office Action shows a plurality of transistors, including transistors 18 and 19. See Takashi, Fig. 6. However, Takashi clearly shows in Figure 6 that the base of transistor 18 is connected to the emitter of transistor 19, and the base of transistor 19 is connected to the collector of transistor 18. *Id.* In contrast, the portion of Kinoshita relied upon in the Office Action discloses a plurality of transistors "connected in parallel with each other and having base, collector, and emitter nodes, respectively, connected to each other." See Kinoshita, claim 1.

It is apparent that modifying Takashi in such a manner as, would be necessary to produce Applicants' invention would require a wholesale reconstruction of Takashi's design, for

which one skilled in the art would have drawn no motivation from either Takashi or Kinoshita. Moreover, the cited teachings of Moyer fail to overcome the deficiencies of Takashi and Kinoshita as discussed above.

Applicants therefore respectfully request the outstanding rejection of Claim 1 be withdrawn and that Claim 1, and its dependents, now be allowed.

Further, independent Claim 6 recites, *inter alia*, a plurality of bipolar transistors that are provided on the semiconductor layer such that collectors, emitters and bases of the bipolar transistors are respectively connected in parallel with each other and resistors are electrically connected to corresponding ones of the plurality of bipolar transistors. An isolation is provided over the main surface of the semiconductor layer to reach the insulation layer and provided such that the isolation surrounds a group of or the whole of the plurality of bipolar transistors, such that the surrounded transistors operate substantially uniformly as constituent elements of a unit transistor.

In addition, independent Claim 10 recites, *inter alia*, a plurality of first bipolar transistors that are provided in a first region over a portion of the semiconductor layer, such that collectors of the first bipolar transistors are connected in parallel with each other, emitters of the first

bipolar transistors are connected in parallel with each other, and bases of the first bipolar transistors are connected in parallel with each other. A first isolation is provided in the main surface of the semiconductor layer to reach the insulation layer, and provided such that the isolation surrounds a group of or the whole of the plurality of first bipolar transistors in the first region, such that the surrounded first bipolar transistors operate substantially uniformly as constituent elements of a first unit transistor. A plurality of second bipolar transistors are provided in a second region over a portion of the semiconductor layer such that collectors of the second bipolar transistors are connected in parallel with each other, emitters of the second bipolar transistors are connected in parallel with each other, and bases of the second bipolar transistors are connected in parallel with each other. A second isolation is provided in the main surface of the semiconductor layer to reach the insulation layer, and provided such that the isolation surrounds each the plurality of second bipolar transistors in a second region, such that the surrounded second bipolar transistors operate substantially uniformly as constituent elements of a second unit transistor.

Independent Claims 6 and 10 are evidently patentable over the combination of Takashi, Kinoshita and Moyer, for at least the reasons presented above with respect to Claim 1.

Applicants therefore respectfully request the outstanding rejections of Claim 6 and 10 be withdrawn and that Claims 6 and 10, and their dependents, now be allowed.

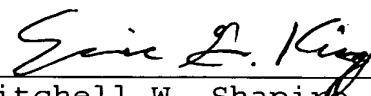
A Notice of Allowance is respectfully requested.

The Commissioner is hereby authorized to charge to Deposit Account No. 50-1165 (XA-10036) any fees under 37 C.F.R. §§ 1.16 and 1.17 that may be required by this paper and to credit any overpayment to that Account. If any extension of time is required in connection with the filing of this paper and has not been separately requested, such extension is hereby requested.

Respectfully submitted,

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